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Diodes Incorporated DMP2021UFDF-7

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DMP2021UFDF

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25℃
-20V	16mΩ @ V _{GS} = -4.5V	-9.0A
	22mΩ @ V _{GS} = -2.5V	-7.7A

Description and Applications

This MOSFET is designed to minimize on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

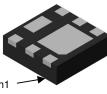
U-DFN2020-6



Notes:



Top View

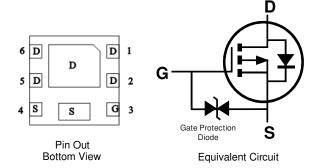


Bottom View

- **Features and Benefits**
- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- ESD protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @
- Weight: 0.007 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2021UFDF-7	U-DFN2020-6	3,000/Tape & Reel
DMP2021UFDF-13	U-DFN2020-6	10,000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

U-DFN2020-6



 $\begin{array}{l} \mathsf{P1} = \mathsf{Product Type Marking Code} \\ \mathsf{YM} = \mathsf{Date Code Marking} \\ \mathsf{Y} = \mathsf{Year} \ (\mathsf{ex: C} = 2015) \\ \mathsf{M} = \mathsf{Month} \ (\mathsf{ex: 9} = \mathsf{September}) \end{array}$

Date Code Key

Year	2014	4	2015		2016	20	17	2018		2019	2	2020
Code	В		С		D			F		G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D





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Maximum Ratings (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	-20	V		
Gate-Source Voltage	V _{GSS}	±8	V		
Continuous Dusin Current (Note C))/ 4 EV	Steady State	T _A = +25 ℃ T _A = +70 ℃	ID	-9.0 -7.2	А
Continuous Drain Current (Note 6) V_{GS} = -4.5V	t<10s	T _A = +25℃ T _A = +70℃	I _D	-11.1 -8.9	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)		I _{DM}	-60	А	
Continuous Source-Drain Diode Current (Note 6)	T _A = +25℃	I _S	-2.4	А	
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	-27	А		
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	38	mJ		

Thermal Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25℃	Р	0.73	W
Total Fower Dissipation (Note 5)	T _A = +70 ℃	PD	0.47	vv
Thermal Desistance, Junction to Ambient (Note 5)	Steady State	Р	172	℃/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ extsf{ heta}JA}$	121	C/W
Total Power Dissipation (Note 6)	T _A = +25℃	D -	2.02	W
Total Fower Dissipation (Note 0)	T _A = +70 ℃	PD	1.30	vv
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	P	63	
memai resistance, sunction to Ambient (Note 6)	t<10s	R _θ JA	42	°C/W
Thermal Resistance, Junction to Case (Note 6)	Steady State	R _{θJC}	18	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	C°

Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

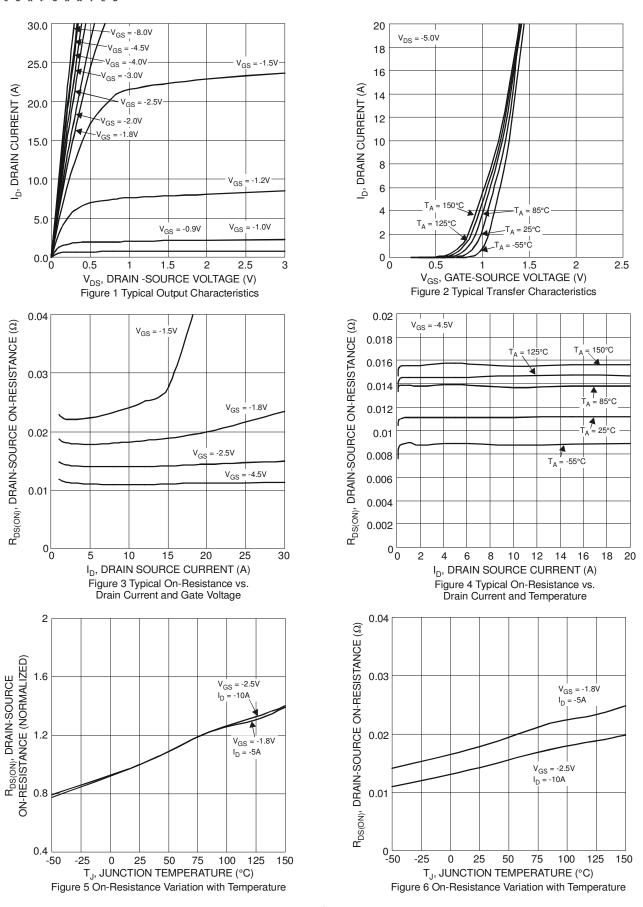
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current T _J = +25 °C	I _{DSS}		—	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	-	_	±10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	-0.35	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			12	16		V _{GS} = -4.5V, I _D = -7.0A
Statia Drain Sauras On Basistanas			15	22		$V_{GS} = -2.5V, I_D = -5.0A$
Static Drain-Source On-Resistance	R _{DS} (ON)	_	19	40	mΩ	$V_{GS} = -1.8V, I_D = -3.0A$
			21	80		V _{GS} = -1.5V, I _D = -1.0A
Diode Forward Voltage	V _{SD}	_	-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -1.0A$
DYNAMIC CHARACTERISTICS (Note 9)	•					
Input Capacitance	Ciss	_	2,760	_		
Output Capacitance	Coss	_	262	_	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	220	—		
Gate Resistance	Rq	_	16	30	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qq	_	34	—		
Total Gate Charge (V _{GS} = -8V)	Qq	_	59	—	nC	
Gate-Source Charge	Q _{gs}		3.5	_	no	$V_{DS} = -15V, I_D = -4.0A$
Gate-Drain Charge	Q _{ad}	_	8.3	—		
Turn-On Delay Time	t _{D(on)}		7.5	_		
Turn-On Rise Time	tr		25	—		$V_{DS} = -15V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t _{D(off)}	_	125	_	ns	$R_{G} = 1\Omega, I_{D} = -4.0A$
Turn-Off Fall Time	tf	_	96	—	1	
Reverse Recovery Time	t _{rr}	_	48	—	ns	I _F = -1.0A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{rr}	_	33	—	nC	I _F = -1.0A, di/dt = 100A/µs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep $T_J = +25$ °C. 8. Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to product testing.

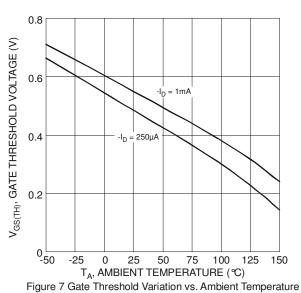


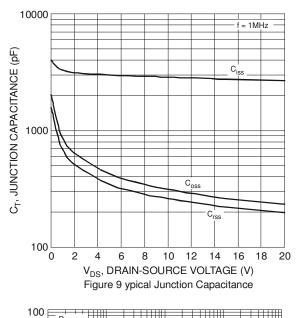


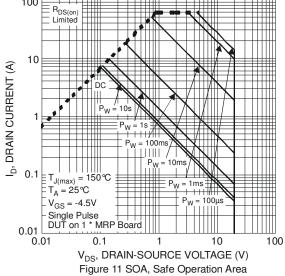
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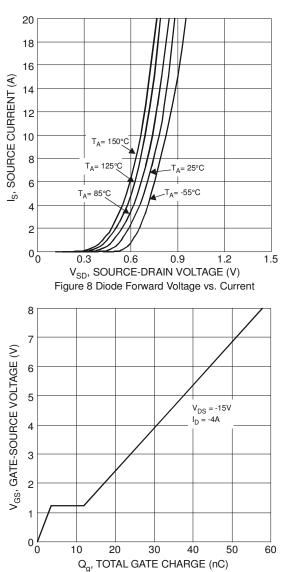
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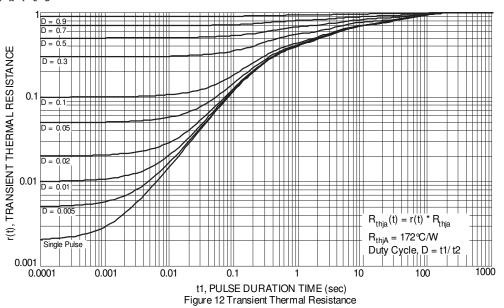
Figure 10 Gate-Charge Characteristics

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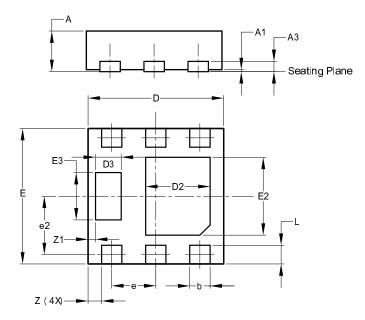




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Package Outline Dimensions

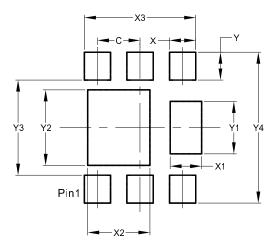
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2020-6 (Type F)								
Dim	Min							
Α	0.57	0.63	0.60					
A1	0	0.05	0.03					
A3	-	-	0.15					
b	0.25	0.35	0.30					
D	1.95	2.05	2.00					
D2	0.85 1.05 0.95							
D3	0.33	0.38						
e	0.65 BSC							
e2	C).863 B	SC					
E	1.95	2.05	2.00					
E2	1.05	1.25	1.15					
E3	0.65	0.75	0.70					
L	0.225 0.325 0.275							
Ζ	0.20 BSC							
Z1	0.110 BSC							
All	All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.650		
Х	0.400		
X1	0.480		
X2	0.950		
X3	1.700		
Y	0.425		
Y1	0.800		
Y2	1.150		
Y3	1.450		
Y4	2.300		





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